

isc Silicon NPN Power Transistor

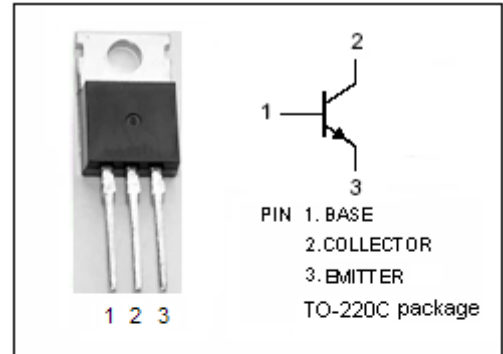
2SD1118

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 50V(\text{Min})$
- High DC Current Gain-
: $h_{FE} = 300V(\text{Min.}) @ I_C = 1A$
- Low Collector Saturation Voltage
- High Reliability

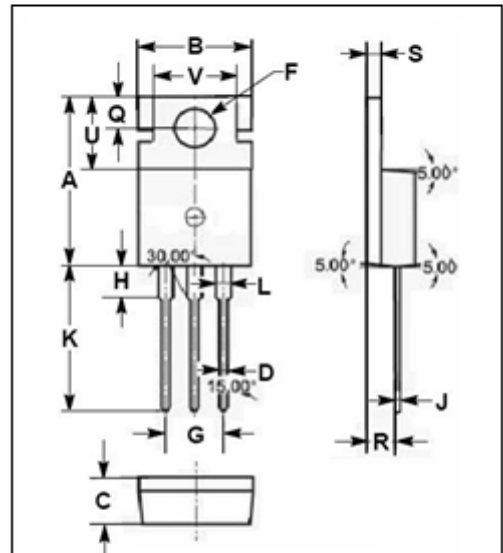
APPLICATIONS

- Switching regulators
- DC-DC converter
- Solid state relay
- General purpose power amplifiers



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	15	V
I_C	Collector Current-Continuous	10	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=0.1\text{mA}; I_E=0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=0.1\text{mA}; I_C=0$	15			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.1\text{A}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.1\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=15\text{V}; I_C=0$			100	μA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	300			

Switching times

t_{on}	Turn-on Time	$I_C=5\text{A}, I_{B1}=-I_{B2}=0.5\text{A};$ $R_L=6\Omega; P_W=20\mu\text{s}; \text{Duty}\leq 2\%$			0.5	μs
t_{stg}	Storage Time				3.0	μs
t_f	Fall Time				0.8	μs